

BUK72150-55A

N-channel TrenchMOS standard level FET Rev. 03 — 26 January 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 3</u> ; see <u>Figure 1</u>	-	-	11	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	36	W
Static chara	Static characteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{\text{Figure 11}};$ see Figure 11	-	127	150	mΩ



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	16	mJ
Dynamic ch	aracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A};$ $V_{DS} = 44 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	2.7	-	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

^[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK72150-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Doromotor	Conditions	Min	May	Hoit
Symbol	Parameter		IVIIII	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 3</u> ; see <u>Figure 1</u>	-	11	Α
		$T_{mb} = 100 ^{\circ}C; V_{GS} = 10 V; see \frac{Figure 1}{}$	-	7	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see <u>Figure 3</u>	-	44	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	36	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	11	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$	-	44	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	16	mJ

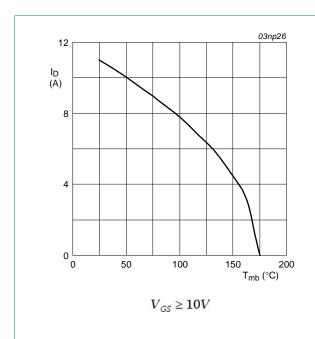


Fig 1. Normalized continuous drain current as a function of mounting base temperature

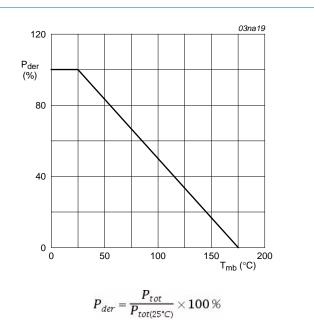
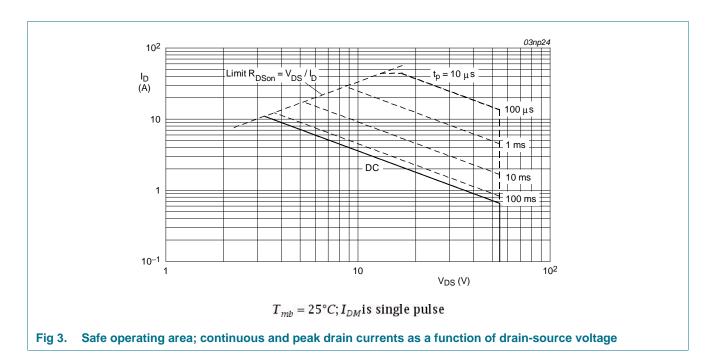


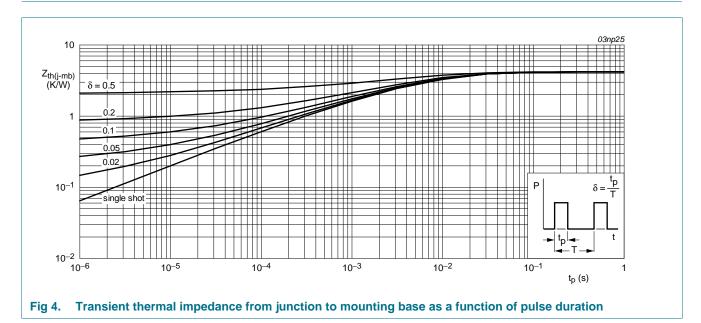
Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	4.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71	-	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
V _{GS(th)} gate-sour voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 9	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 9	1	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 9	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}$; $I_D = 5 \text{ A}$; $T_j = 175 \text{ °C}$; see Figure 10; see Figure 11	-	-	300	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 10; see Figure 11	-	127	150	mΩ
Dynamic (characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 3 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	5.5	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 12</u>	-	1	-	nC
Q_{GD}	gate-drain charge		-	2.7	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	242	322	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 13</u>	-	40	48	pF
C _{rss}	reverse transfer capacitance		-	25	35	pF
d(on)	turn-on delay time	$V_{DS} = 25 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 ^{\circ}C$	-	26	-	ns
t _{d(off)}	turn-off delay time		-	8	-	ns
t _f	fall time	V_{DS} 25 V; R_{L} = 2.7 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5.6 Ω ; T_{j} = 25 °C	-	10	-	ns
L _D	internal drain inductance	measured from drain to center of die ; $T_j = 25~^{\circ}\text{C}$	-	2.5	-	nΗ
-S	internal source inductance	measured from source lead to source bond pad; $T_j = 25$ °C	-	7.5	-	nΗ
Source-dr	rain diode					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 14	-	1.25	1.5	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	32	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	50	-	nC

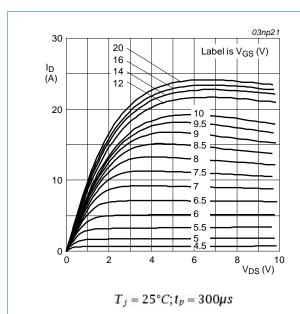


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

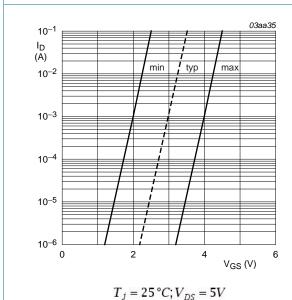


Fig 7. Sub-threshold drain current as a function of gate-source voltage

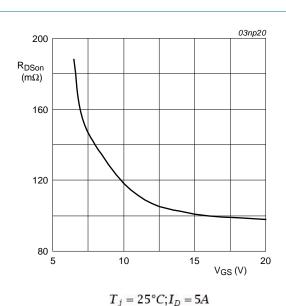


Fig 6. Drain-source on-state resistance as a function

of gate-source voltage; typical values

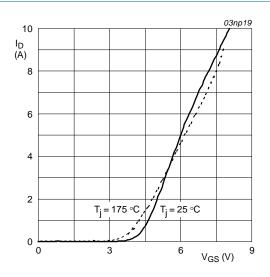
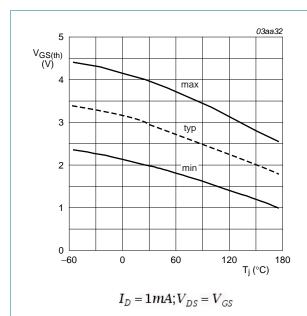


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

 $V_{DS} = 25V$

03np22



Gate-source threshold voltage as a function of Fig 9. junction temperature

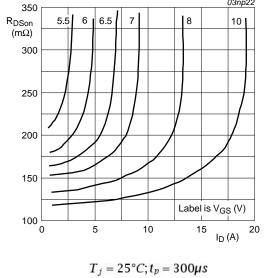


Fig 10. Drain-source on-state resistance as a function

of drain current; typical values

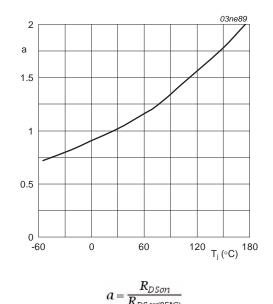


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

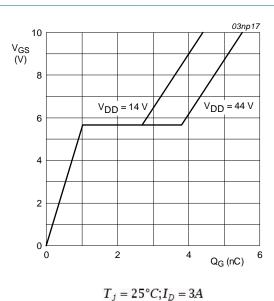


Fig 12. Gate-source voltage as a function of gate charge; typical values

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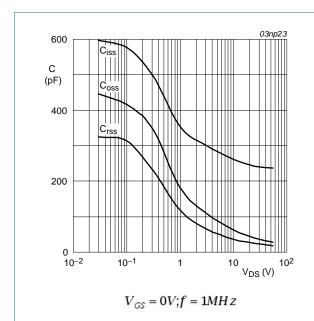


Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

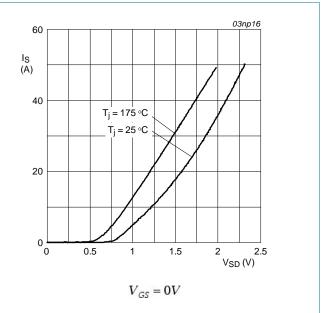


Fig 14. Source current as a function of source-drain voltage; typical values

7. Package outline

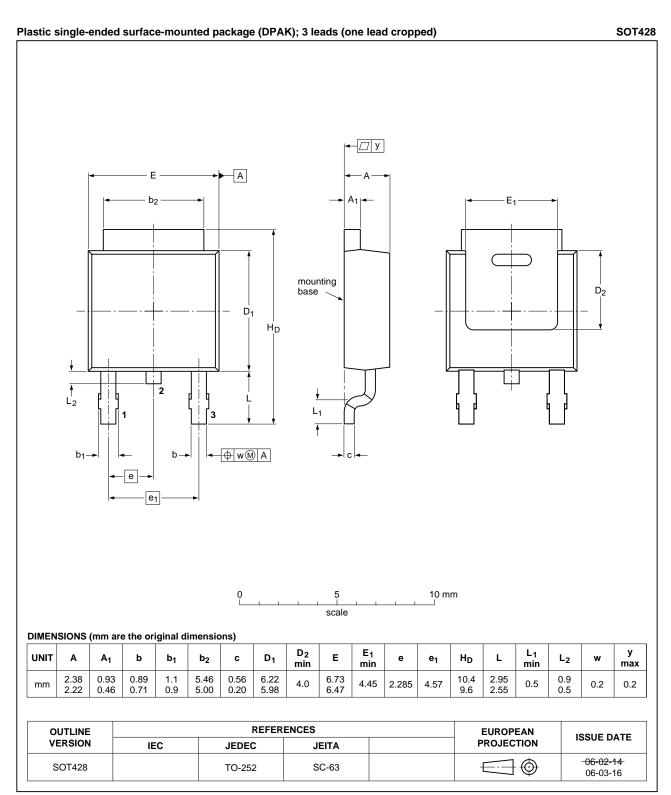


Fig 15. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK72150-55A v.3	20110126	Product data sheet	-	BUK72150-55A v.2		
Modifications:	of NXP Semico	nductors. e been adapted to the new		th the new identity guidelines e appropriate.		
BUK72150-55A v.2 (9397 750 12335)	20031120	Product data sheet	-	-		

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9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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